Fuji Power MOSFET SuperFAP-G series Target Specification ***PRELIMINARY***

2SK3674-01L,S,SJ (900V/2.0Ω/7A)

1) Package T-PACK L ･･･**See Page 2/4**
S ･･･See Page 3/4
SJ ･･･See Page 4/4

2) Absolute Maximum Ratings (Tc=25℃ unless otherwise specified)

Items	Symbols	Ratings	Units	
Drain-Source Voltage	V_{DS}	900	V	
Continuous Drain Current	I_D	±7	A	
Pulsed Drain Current	$I_{D(pulse)}$	±28	A	
Gate-Source Voltage	V_{GS}	±30	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	I_{AR}	7	A	
Non-Repetitive Maximum Avalanche Energy	E_{AS}	269.5	mJ	*1
Maximum Drain-Source dV/dt	dVDS/dt	20	kV/us	
Peak Diode recovery dV/dt	dV/dt	5	kV/us	*2
Maximum Power Dissipation	$P_{D\ @Tc=25℃}$	225	W	
	$P_{D\ @Ta=25℃}$	1.67	W	
Operating and Storage Temperature range	T_{ch}	150	℃	
	T_{stg}	-55 ～ +150	℃	

3)Electrical Characteristics (Tch=25℃ unless otherwise specified)

Items	Symbols	Test Conditions		min.	typ.	max.	Units
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250uA	V_{GS}=0V	900	---	---	V
Gate Threshold Voltage	V_{GS}(th)	I_D=250uA	V_{DS}=V_{GS}	3.0	---	5.0	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=900V	T_{ch}=25℃	---	---	50	μA
		V_{GS}=0V	T_{ch}=125℃	---	---	500	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V	V_{DS}=0V	---	---	100	nA
Drain-Source On-State Resistance	R_{DS}(on)	I_D=3.5A	VGS=10V	---	---	2.0	Ω
Input Capacitance	C_{iss}	V_{DS}=25V		---	980	---	pF
Output Capacitance	C_{oss}	V_{GS}=0V		---	120	---	
Reverse Transfer Capacitance	C_{rss}	f=1MHz		---	6	---	
Total Gate Charge	Qg	Vcc=450V		---	28	---	nC
Gate to Source Charge	Qgs	I_D=7A		---	9	---	
Gate to Drain (Miller) Charge	Qgd	V_{GS}=10V		---	8	---	
Avalanche Capability	I_{AV}	L=10.1mH	Tch=25℃	7	---	---	A
Diode Forward On-Voltage	V_{SD}	I_F=7A,VGS=0V,Tch=25℃		---	1.0	1.5	V

4) Thermal Characteristics

Items	Symbols	Test Conditions	min.	typ.	max.	Units
Channel to Case	Rth(ch-c)				0.56	℃/W
Channel to Ambient	Rth(ch-a)				75.0	℃/W

*1 L=10.1mH,Vcc=90V
***2 I_F≤-I_D,-di/dt=50A/μs,Vcc≤BV_{DSS},Tch≤150°C**

	DATE	NAME	APPROVED
DRAWN	Sep.-10-'02	T. Kubozama	T. HOSEN
CHECKED	Sep.-10-'02	T. Yamada	
REVISIONS			

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DWG.NO. **MT5F12615 1/4**

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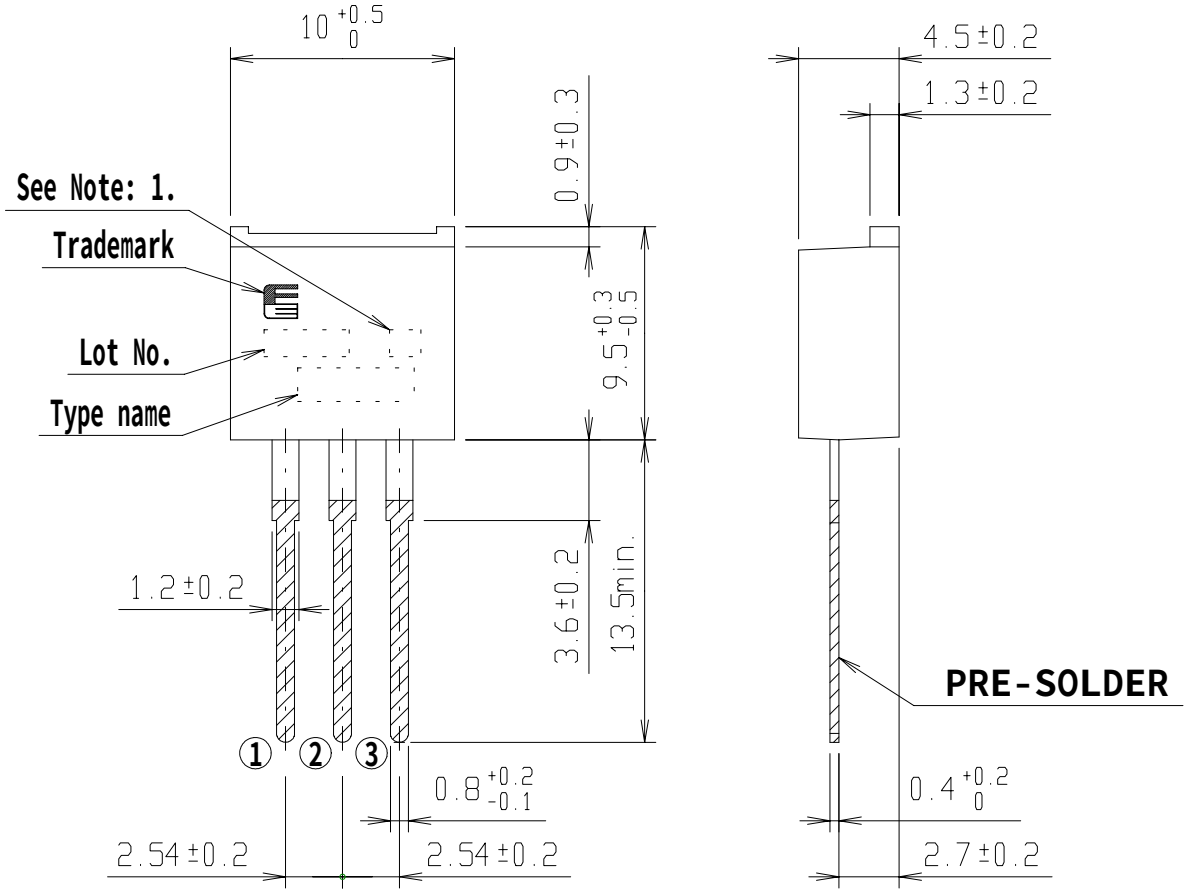
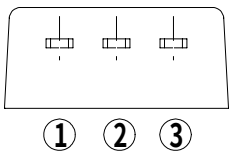
FUJI POWER MOS FET





CONNECTION

① GATE
② DRAIN
③ SOURCE

JEDEC : TO-220AB

Note: 1. Guaranteed mark of avalanche ruggedness.

DIMENSIONS ARE IN MILLIMETERS.

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OUT VIEW

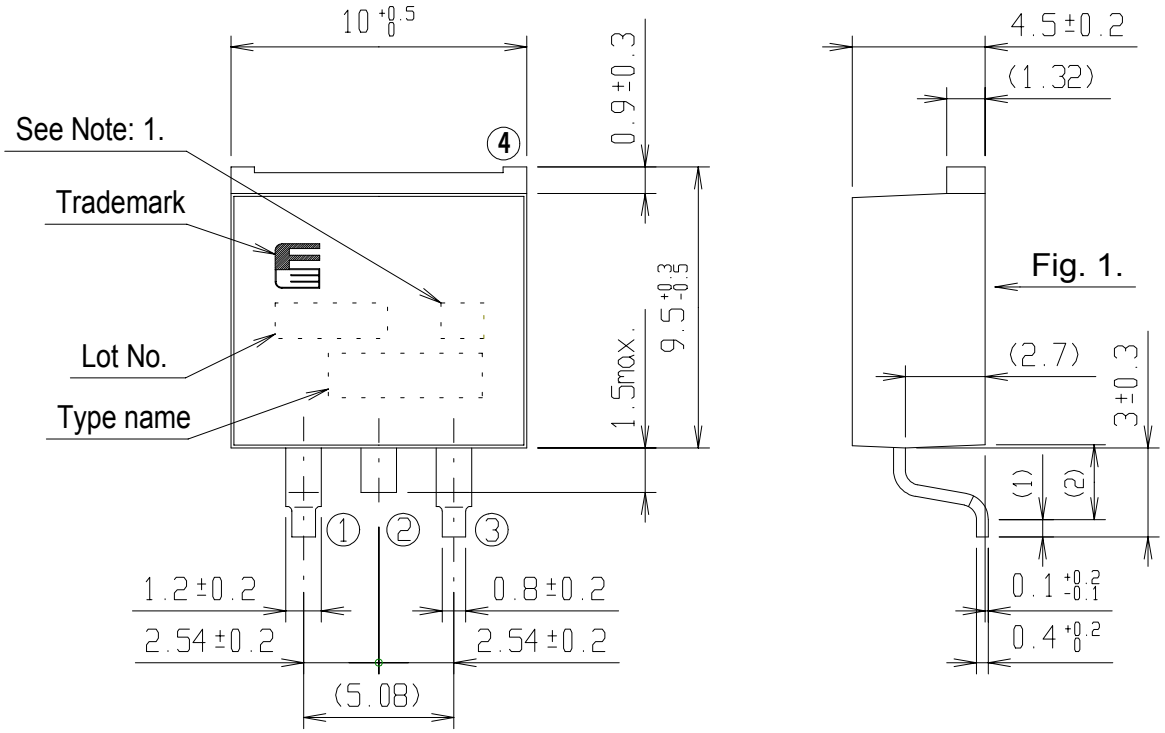
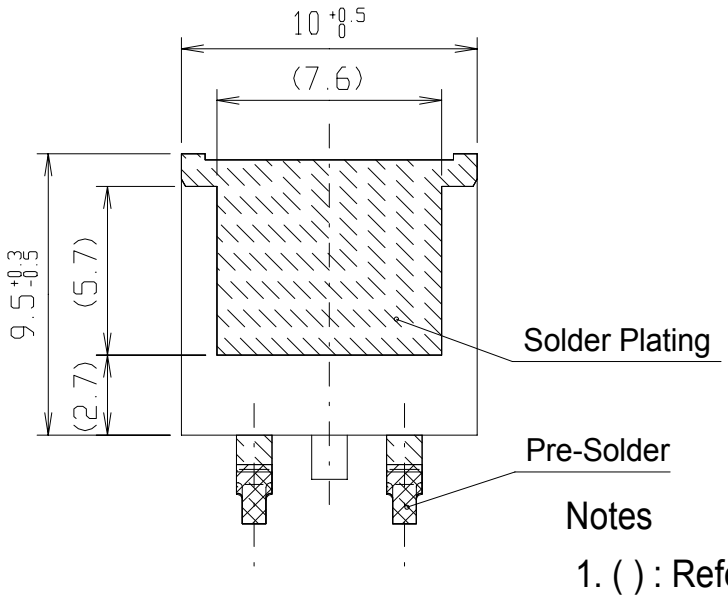


Fig. 1.



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CONNECTION

① GATE
④ ② DRAIN
③ SOURCE

Notes

1. ( ) : Reference dimensions.
2. The metal part is covered with the solder plating, part of cutting is without the solder plating.

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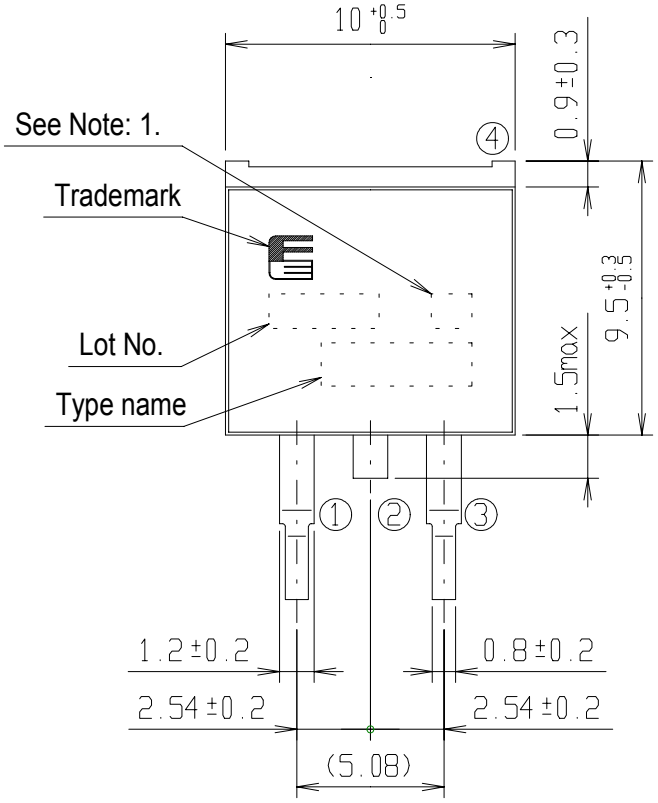
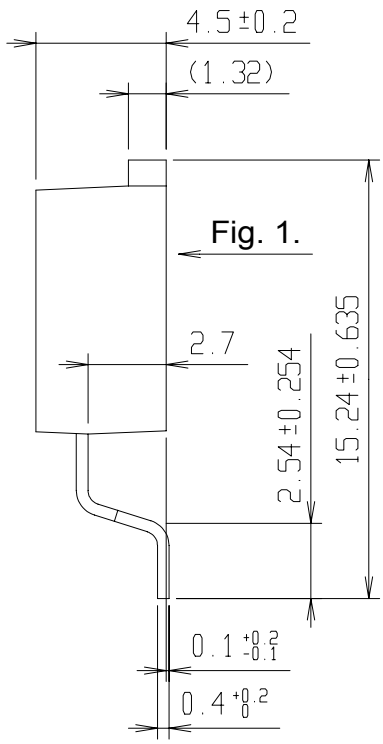
OUT VIEW





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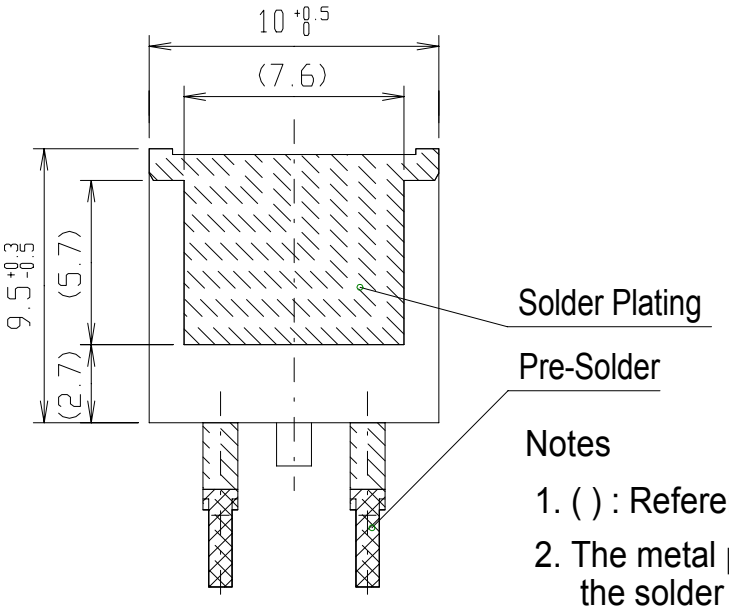

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